

## Silicon NPN Power Transistors

## 2SD201

## DESCRIPTION

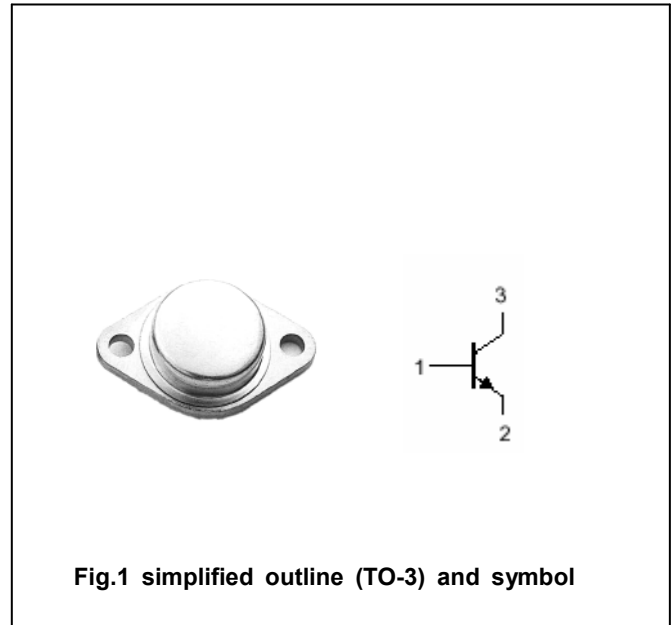
- With TO-3 package
- Large current capability
- Wide area of safe operation

## APPLICATIONS

- For power amplifier and switching applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a = \square$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	90	V
$V_{CEO}$	Collector-emitter voltage	Open base	60	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		6	A
$P_C$	Collector power dissipation	$T_C = 25 \square$	50	W
$T_j$	Junction temperature		150	$\square$
$T_{stg}$	Storage temperature		-55~150	$\square$

**Silicon NPN Power Transistors****2SD201****CHARACTERISTICS**T<sub>j</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =0	60			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A			2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A			2.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =90V ; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =4V	40			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =12V		8		MHz

PACKAGE OUTLINE

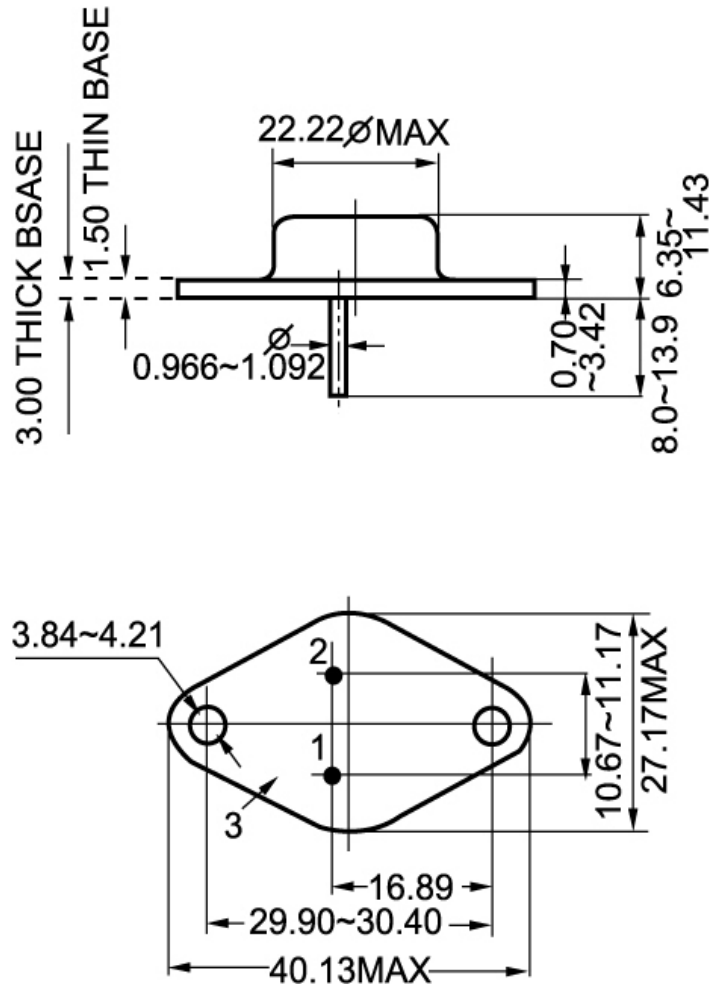


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)